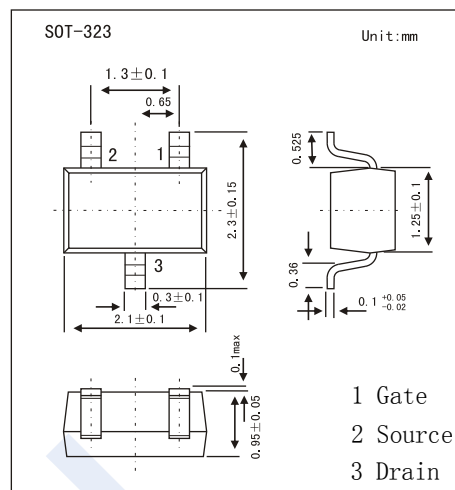


P-Channel MOSFET

KI001PW

■ Features

- $V_{DS} (V) = -15V$
- $I_D = -3 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 85m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 95m\Omega (V_{GS} = -2.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-15	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-3	A
Power Dissipation	P_D	0.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -15V, V_{GS} = 0V, T_J = 25^\circ C$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 10V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3A$			85	m Ω
		$V_{GS} = -2.5V, I_D = -2A$			95	

■ Marking

Marking	001P
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